

इंडियन इंस्टीट्यूट ऑफ टेक्नोलॉजी दिल्ली
हौज खास, नई दिल्ली -110016
(औद्योगिक अनुसंधान एवं विकास इकाई)
INDIAN INSTITUTE OF TECHNOLOGY DELHI
Hauz Khas, New Delhi-110016
(Industrial Research & Development Unit)

No. IITD/IRD/RP04924G/ 512909

Dated:28/04/2026

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Applications from Indian nationals are invited for Project Appointment under the following project. Appointment shall be on contractual basis with consolidated pay, renewable yearly or upto the duration of the project, whichever is earlier. निम्नलिखित परियोजना के तहत भारतीय नागरिकों से आवेदन आमंत्रित किए जाते हैं। अपॉइंटमेंट, अनुबंधित आधार पर समेकित वेतन, नवीकरणीय वार्षिक या परियोजना की अवधि तक, जो भी पहले हो, के साथ होगा.

Title of the Project	Building Blocks for 6G THz Communication System Front Ends (RP04924G)	
Funding Agency	Centre for Development of Telematics, New Delhi	
Name of the Project Investigator	Prof. Ananjan Basu [email ID: ananjan@care.iitd.ac.in]	
Deptt./Centre	Centre for Applied Research in Electronics (CARE)	
Duration of the Project	Upto:20/03/2028	
Post (s)	Consolidated fellowship / Pay-slab	Qualifications
Sr. Project Scientist (01)	Rs.60,750-62,570-64,450-66,380-68,370-70,420-72,530-74,710-76,950-79-260/- p.m. plus HRA @ 30%	Essential: 1 st class M.Tech or M.Sc. (with three years of relevant experience) in relevant subject and experience in Semiconductor Devices, hands on experience on device fabrication including lithography and metallization, Preferable: PhD (thesis submitted is acceptable), Experience in Frequency domain THz measurements
Sr. Project Scientist (01)	Rs.60,750-62,570-64,450-66,380-68,370-70,420-72,530-74,710-76,950-79-260/- p.m. plus HRA @ 30%	Essential: 1 st class M.Tech. or M.Sc. (with three years of relevant experience) in relevant subject and experience in Semiconductor Devices, hands on experience on device fabrication including lithography and metallization, Preferable: PhD (thesis submitted is acceptable), EBL/nano lithography, Magnetic device fabrication, characterization.
Sr. Project Scientist (01)	Rs.60,750-62,570-64,450-66,380-68,370-70,420-72,530-74,710-76,950-79-260/- p.m. plus HRA @ 30%	Essential: 1 st class M.Tech. or M.Sc. (with three years of relevant experience) in relevant subject and experience in Semiconductor Devices, hands on experience on device fabrication. Preferable: PhD (thesis submitted is acceptable), RF device simulation and measurements.
Project Scientist (01)	Rs.47,790-49,220-50,700-52,220-53,790-55,400-57,060-598,770-60,530-62,350/-p.m. plus HRA @ 30%	Essential: 1 st class B.Tech. in EE/ECE with mastery of CMOS Analog and RF circuit design. Preferable: Knowledge of Cadence virtuoso.
Project Scientist (01)	Rs.47,790-49,220-50,700-52,220-53,790-55,400-57,060-598,770-60,530-62,350/-p.m. plus HRA @ 30%	Essential: 1 st class B.Tech. in Electronics or equivalent. M.Tech. strongly preferred. Experience in 3DEM simulation, design of mm-wave circuits and design of waveguide components desirable.
Jr. Project Assistant (Tech.) (01)	Rs.29,290-30,170-31,080-32,010-32,970-33,960-34,980-36,030-37,100-38,220/-p.m. plus HRA @ 30%	Diploma (3 years duration)/Graduate Degree in appropriate discipline OR ITI (2 years duration) in relevant trade with 6 years relevant work experience. Basic knowledge of semiconductor lab processes, equipment and materials desirable.

The posts may be downgraded as per discretion of the Selection Committee if none of the candidate is found suitable for the post.

The candidates who are interested to apply for the above post should download Form No. IRD/REC-4 from the IRD Website (<http://ird.iitd.ac.in/rec>) of IIT Delhi and submit the duly filled form with complete information regarding educational qualifications indicating percentage of marks/division, details of work experience etc. by e-mail with advertisement No. on the subject line to Prof. Ananjan Basu at email ID: ananjan@care.iitd.ac.in

